

NPN SILICON PLANAR HIGH VOLTAGE TRANSISTOR

FXTA42

ISSUE 1 – SEPT 93

FEATURES

- * 300 Volt V_{CEO}

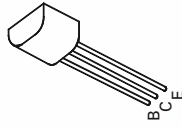
APPLICATIONS

- * Telephone dialler circuits

REFER TO MPSA42 FOR GRAPHS

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	300	V
Collector-Emitter Voltage	V_{CEO}	300	V
Emitter-Base Voltage	V_{EBO}	6	V
Continuous Collector Current	I_C	500	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	680	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +175	$^\circ\text{C}$



E-Line

TO92 Compatible

查询FXTA42供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	300			V	$I_C=100\mu\text{A}, I_E=0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	300			V	$I_C=1\text{mA}, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6			V	$I_E=100\mu\text{A}, I_C=0$
Collector Cut-Off Current	I_{CBO}			0.1	μA	$V_{CB}=200\text{V}, I_E=0$
Emitter Cut-Off Current	I_{EBO}			0.1	μA	$V_{EB}=6\text{V}, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5	V	$I_C=20\text{mA}, I_B=2\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	$I_C=20\text{mA}, I_B=2\text{mA}$
Static Forward Current Transfer Ratio	h_{FE}	25 40 40				$I_C=1\text{mA}, V_{CE}=10\text{V}^*$ $I_C=10\text{mA}, V_{CE}=10\text{V}^*$ $I_C=30\text{mA}, V_{CE}=10\text{V}^*$
Transition Frequency	f_T	50			MHz	$I_C=10\text{mA}, V_{CE}=20\text{V}$ $f=20\text{MHz}$
Output Capacitance	C_{obo}			6	pF	$V_{CB}=20\text{V}, f=1\text{MHz}$

